

1SS110

Silicon Epitaxial Planar Diode for Tuner Band Switch

HITACHI

ADE-208-179B (Z)
Rev. 2

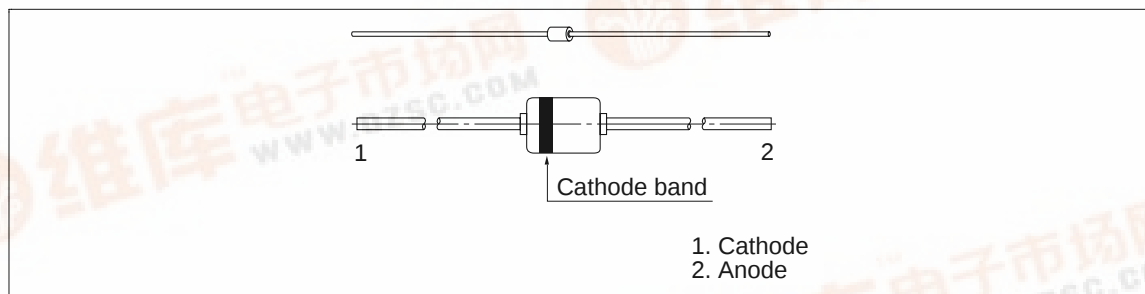
Features

- Low forward resistance. ($r_f = 0.9\Omega_{\text{max}}$)
- Suitable for 5mm pitch high speed automatic insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Package Code
1SS110	Verdure	MHD

Outline



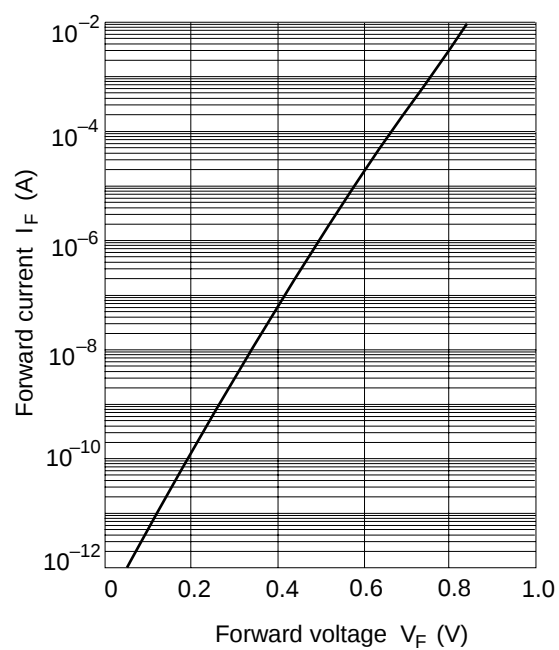
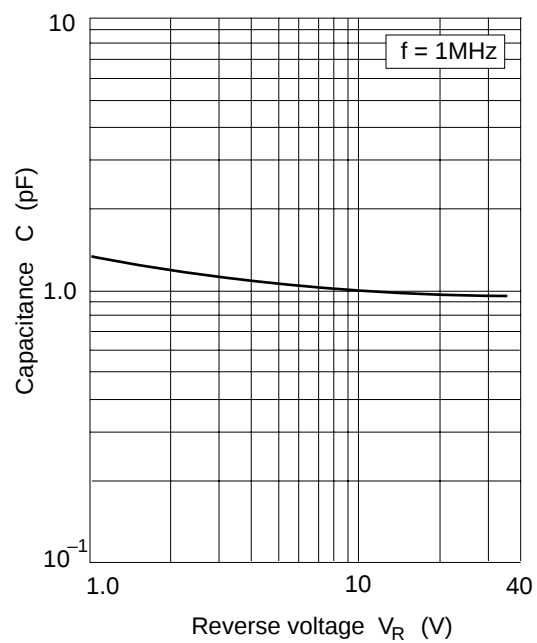
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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V _R	35	V
Forward current	I _F	100	mA
Junction temperature	T _j	175	°C
Storage temperature	T _{stg}	−65 to +175	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V _F	—	—	1.0	V	I _F = 10mA
Reverse voltage	V _R	35	—	—	V	I _R = 10μA
Reverse current	I _R	—	—	0.1	μA	V _R = 25V
Capacitance	C	—	—	1.2	pF	V _R = 6V, f = 1MHz
Forward resistance	r _f	—	—	0.9	Ω	I _F = 2mA, f = 100MHz

**Fig.1 Forward current Vs. Forward voltage****Fig.2 Capacitance Vs. Reverse voltage**

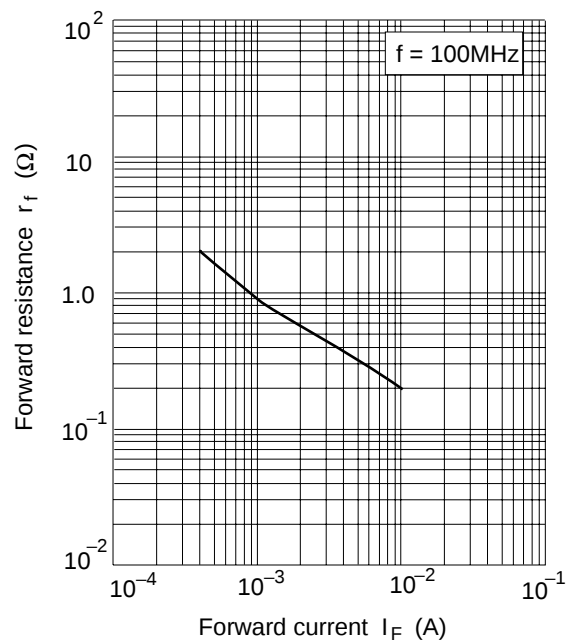


Fig.3 Forward resistance Vs. Forward current

Package Dimensions

